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U.S. Department of Commerce, Patent and Trademark Office		Atty. Docket No.		Serial No.			
		M-15327 US		Unassigned			
INFORMATION		DISCLOSURE STATEMENT BY APPLICANT		Applicant(s)			
		(attach several sheets if necessary)		Chia-Shun Hsiao et al.			
		Filing Date		Group			
		Herewith		Unassigned			
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
CAE	AA	03/0067806	10 Apr. 2003	Tuan	—	—	—
CAE	AB	555,524	12 Mar. 2002	Tuan et al.	—	—	—
CAE	AC	541,324	1 Apr. 2003	Wang	—	—	—
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
Foreign Patent Documents							
						Translation	
		Document	Date	Country	Class	Subclass	Yes No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
Naruke et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on Its Source Side", IBM Technical Digest 1989, pages 603-606.							
United States Application No.: 10/402,698 filed March 28, 2003 by Chung et al.							
Chih et al., "0.18um Modular Triple Self-Aligned Embedded Split-Gate Flash Memory", 2000 Symposium on VLSI Technology, Digest of Technical Papers, pages 120-121.							
Examiner		Date Considered	7/25/05				
*EXAMINER: citation if not in							